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(Approved by AICTE, New Delhi & Govt. of Karnataka)

(Autonomous Institute, Affiliated to VTU)
Accredited by NBA & NAAC with 'A' Grade

SEMESTER END EXAMINATIONS FEBRUARY - MARCH 2021

Program	: B.E. : Electronics and Communication Engineering	Semester	: III
Course Name	: Analog Circuits	Max. Marks	: 100
Course Code	: EC32	Duration	: 3 Hrs

Instructions to the Candidates:

- Answer one full question from each unit.

UNIT- I

1. a) Find V_y using mesh current analysis for the circuit as shown in Fig.1(a). CO1 (10)

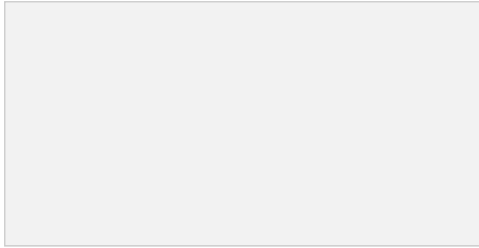


Fig.1(a)

- b) Convert the given circuit as shown in Fig.1(b) into a current source in parallel with a resistor across A - B. CO1 (10)

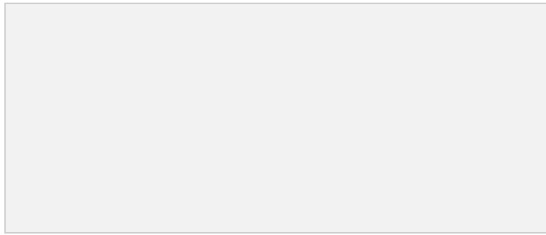


Fig.1(b)

2. a) Find the equivalent resistance between terminals AB using star - delta transformation for the network as shown in Fig.2(a). CO1 (10)

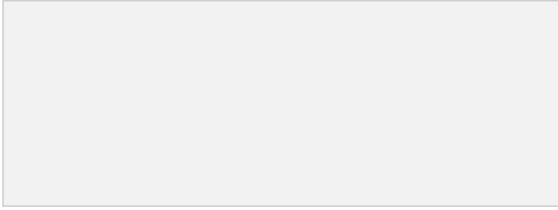


Fig.2(a)

- b) Using nodal analysis find i_1 and i_3 currents in the circuit shown in Fig.2(b). CO1 (10)

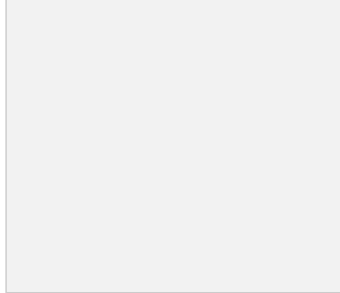
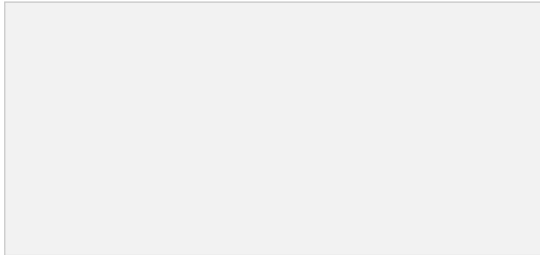


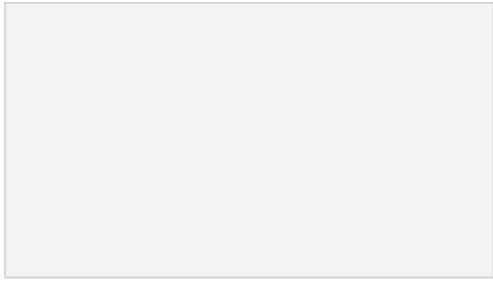
Fig.2(b)

UNIT – II

3. a) State and Prove Superposition theorem. CO2 (10)
 b) Find the thevenin's equivalent network which includes a dependent source as shown in Fig.3(b). CO2 (10)



4. a) State and prove thevenin's theorem. CO2 (10)
 b) For the circuit as shown in Fig.4(b), find the value of R_L which results in maximum power transfer. Also calculate the value of the maximum power. CO2 (10)



UNIT – III

5. a) State the advantages and disadvantages of h-parameters and draw the small signal model of CE amplifier. CO3 (05)
- b) Show that negative feedback decreases the output resistance of voltage series feedback amplifier. CO3 (06)
- c) The transistor with $h_{ie}=1k\Omega$, $h_{fe}=60$, $h_{re}=205 \times 10^{-4}$, $h_{oe}=25 \times 10^{-6}$ A/V. is connected in CE configuration as shown in Fig.5(c). Calculate: $A_i = I_o/I_i$, A_v , R_i , R_o . CO3 (09)

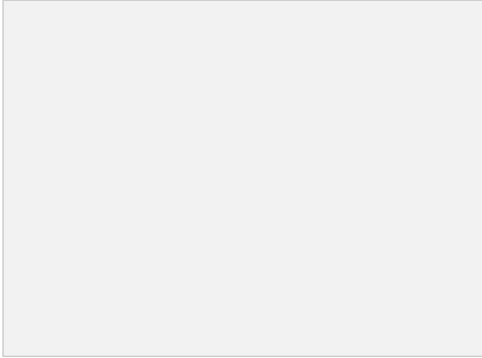


Fig.5(c)

6. a) The transistor used in the circuit as shown in Fig.6(a) has the following parameters, $h_{fe}=60$, $h_{ie}=500\Omega$, $h_{oe}=1/40K$ and $h_{re}=2.4 \times 10^{-4}$. Calculate R_i , R_o , A_i , A_v and A_{vs} . CO3 (09)

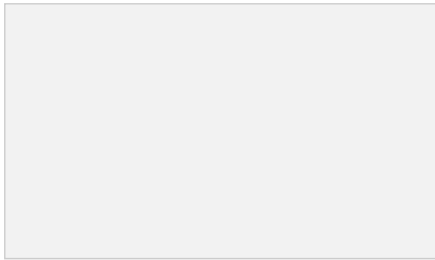


Fig.6(a)

- b) A voltage amplifier has the following parameter values without feedback. CO3 (06)
 Open circuit voltage gain $A_v = -500$
 Input resistance $R_i = 2 \text{ k}\Omega$
 Output resistance $R_o = 402 \text{ k}\Omega$
 Bandwidth $BW = 300 \text{ KHz}$
 Load resistance $R_L = 10 \text{ KHz}$
 If 10% negative voltage series feedback is given. Calculate $A_{v_{fr}}$, R_{if} and BW_{fr} .
- c) State and prove Miller's Dual theorem. CO3 (05)

UNIT – IV

7. a) Derive an expression for the output power and conversion efficiency of a transformer coupled class B push pull power amplifier. CO4 (08)
- b) With neat sketches explain the thermal analogy of a power transistor. CO4 (04)
- c) Design a single ended class A power amplifier and draw the circuit with proper design components to meet the following specifications. CO4 (08)
 i) Maximum 400mW to be delivered to a load of 8Ω
 ii) Transformer efficiency of 80%
 iii) Power supply available of 7V
 Transistors available
 i) SL100 with $(P_d)_{\max} = 500 \text{ mW}$
 ii) 2N 176 with $(P_d)_{\max} = 10 \text{ W}$
 iii) 40309 with $(P_d)_{\max} = 2.5 \text{ W}$
8. a) State the heat sink selection criterion for a transistor operating with $V_{CE} = 20 \text{ V}$ and $I_C = 1.5 \text{ A}$. Its thermal resistance from junction to case is 1°C/W . The junction temperature should not exceed 85°C if the ambient temperature is 25°C . CO4 (07)
- b) With neat sketches explain the operation of class C power amplifier. CO4 (08)
- c) A power amplifier has harmonic distortions $D_2 = 0.1$, $D_3 = 0.02$, $D_4 = 0.01$, the fundamental current $I_1 = 4 \text{ A}$ and $R_L = 8\Omega$. Calculate the total harmonic distortion, fundamental power and total power. CO4 (05)

UNIT – V

9. a) Explain the V-I characteristics of an N-channel E-MOSFET with neat sketches? CO5 (06)
- b) To establish a dc current $I_D = 0.5 \text{ mA}$, the MOSFET is specified to have $V_T = 1 \text{ V}$, $K_n W/L = 1 \text{ mA/V}^2$, $\lambda = 0$, $V_{DD} = 15 \text{ V}$. Calculate %change in I_D when MOSFET is replaced having the same $K_n W/L$ but $V_T = 1.5 \text{ V}$ as shown in Fig.9(b) CO5 (10)